

## N-channel Enhancement Mode Power MOSFET

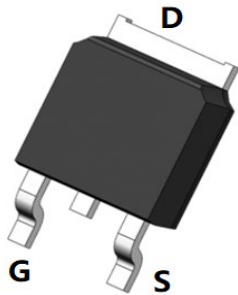
### Features

- $V_{DS} = 60V$ ,  $I_D = 50A$   
 $R_{DS(ON)} < 12\ m\Omega$  @  $V_{GS} = 10V$   
 $R_{DS(ON)} < 16\ m\Omega$  @  $V_{GS} = 4.5V$

### General Features

- Advanced Trench Technology
- Provide Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead Free and Green Available

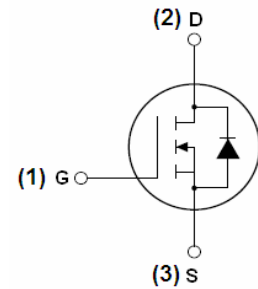
100% UIS TESTED!  
 100%  $\Delta V_{ds}$  TESTED!



TO-252-2L Top View



Pin Assignment



Schematic Diagram

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	50	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	35.4	A
Pulsed Drain Current	$I_{DM}$	200	A
Maximum Power Dissipation	$P_D$	85	W
Derating factor		0.57	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	200	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	1.8	$^\circ C/W$
--	-----------------	-----	--------------

**Electrical Characteristics: ( $T_C=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		3.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	12		m $\Omega$
		$V_{GS}=4.5V, I_D=20A$	-	16		m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=20A$	18	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=30V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	1630	-	PF
Output Capacitance	$C_{oss}$		-	113	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	97	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, R_L=6.7\Omega$ $V_{GS}=5V, R_G=3\Omega$	-	15	-	nS
Turn-on Rise Time	$t_r$		-	20	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	120	-	nS
Turn-Off Fall Time	$t_f$		-	15.6	-	nS
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, R_L=6.7\Omega$ $V_{GS}=10V, R_G=3\Omega$	-	7.4	-	nS
Turn-on Rise Time	$t_r$		-	5.1	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	28.2	-	nS
Turn-Off Fall Time	$t_f$		-	5.5	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=30V, I_D=20A,$ $V_{GS}=10V$	-	39		nC
Gate-Source Charge	$Q_{gs}$		-	7		nC
Gate-Drain Charge	$Q_{gd}$		-	8.5		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=20A$	-		1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	50	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = 20A$ $di/dt = 100A/\mu\text{s}$ (Note 3)	-	28	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	40	-	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, L=0.5\text{mH}, R_G=25\Omega$

Typical Electrical and Thermal Characteristics (Curves)

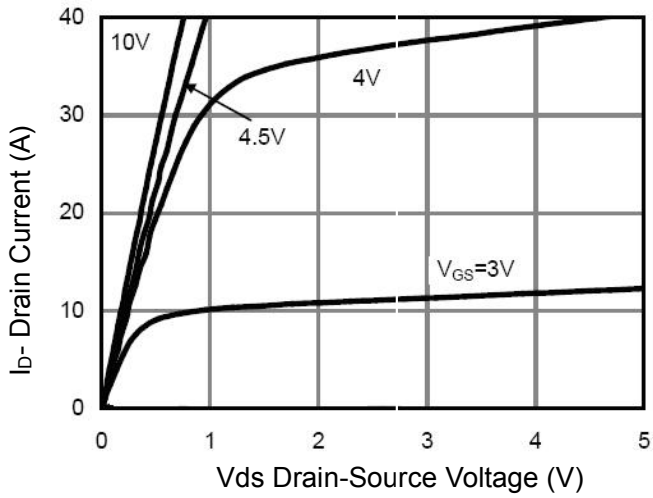


Figure 1 Output Characteristics

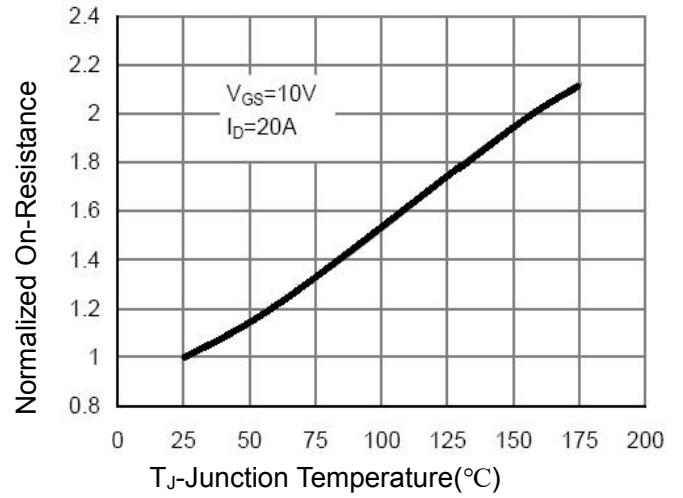


Figure 4 Rds(on)-Junction Temperature

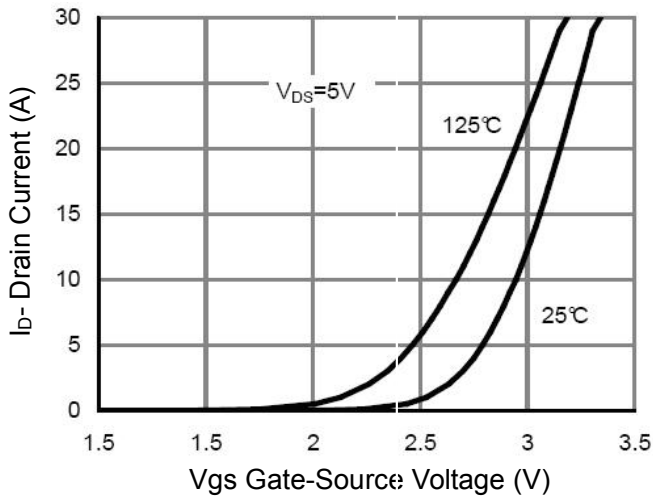


Figure 2 Transfer Characteristics

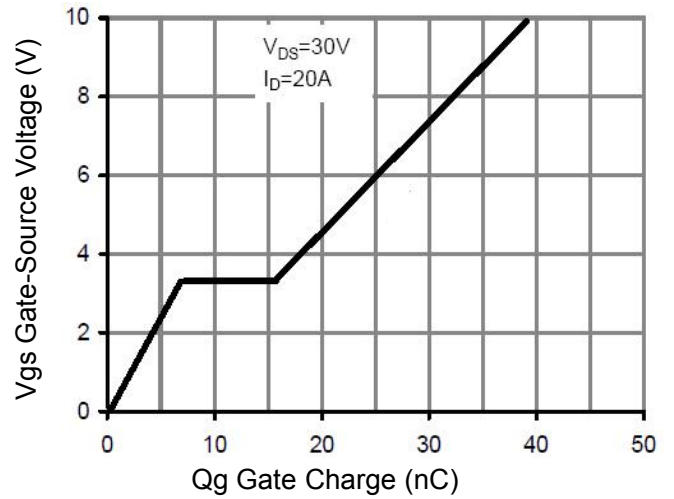


Figure 5 Gate Charge

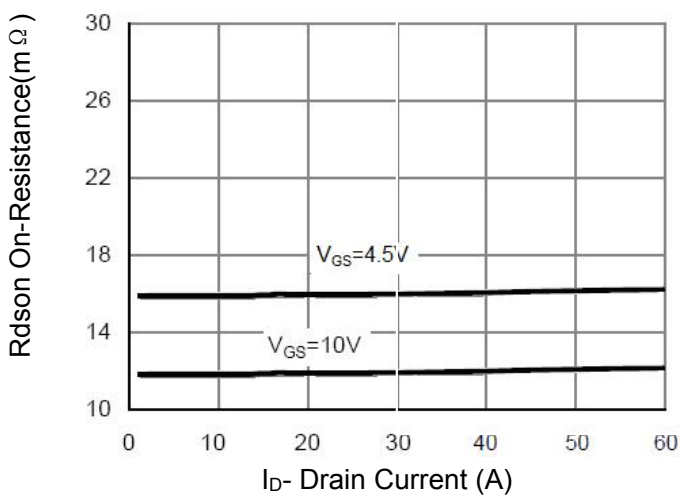


Figure 3 Rds(on)- Drain Current

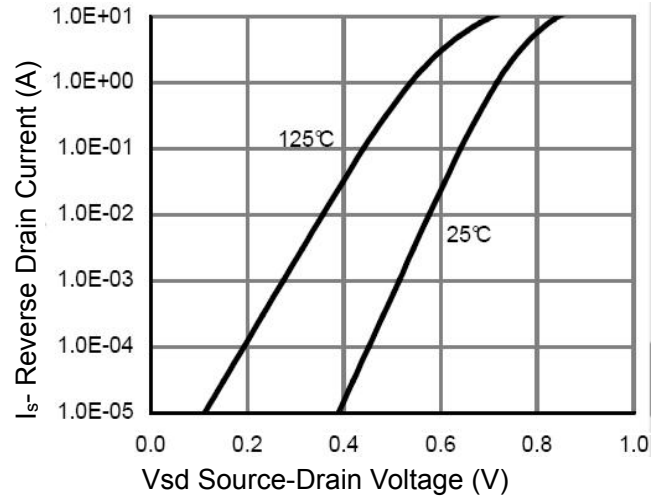


Figure 6 Source- Drain Diode Forward

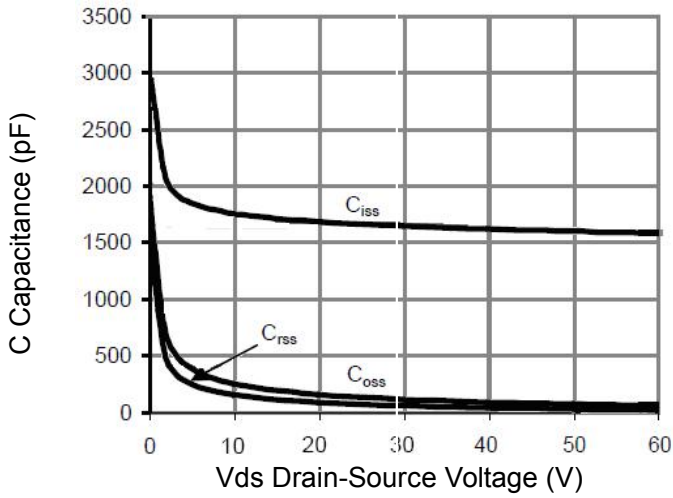


Figure 7 Capacitance vs Vds

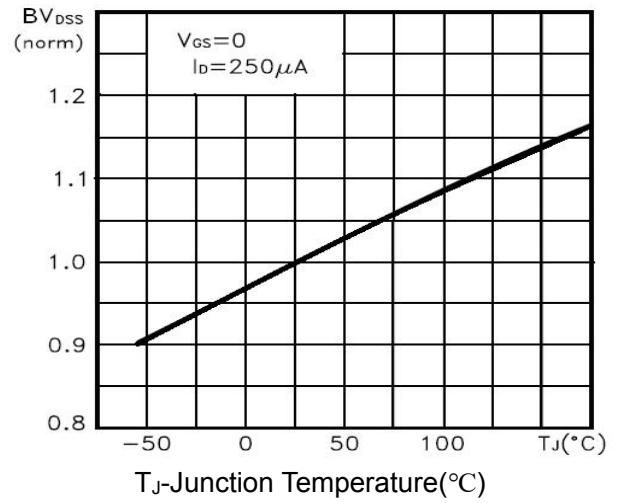


Figure 9  $BV_{DSS}$  vs Junction Temperature

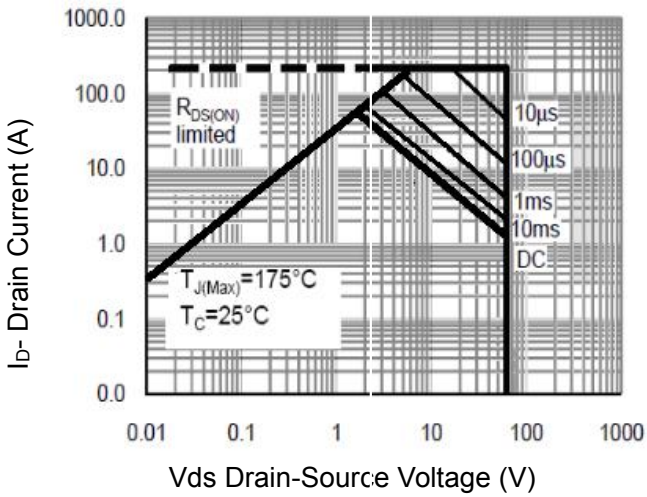


Figure 8 Safe Operation Area

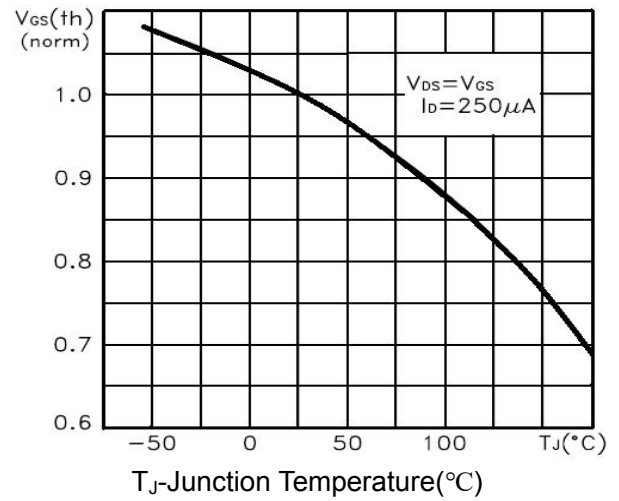


Figure 10  $V_{GS(th)}$  vs Junction Temperature

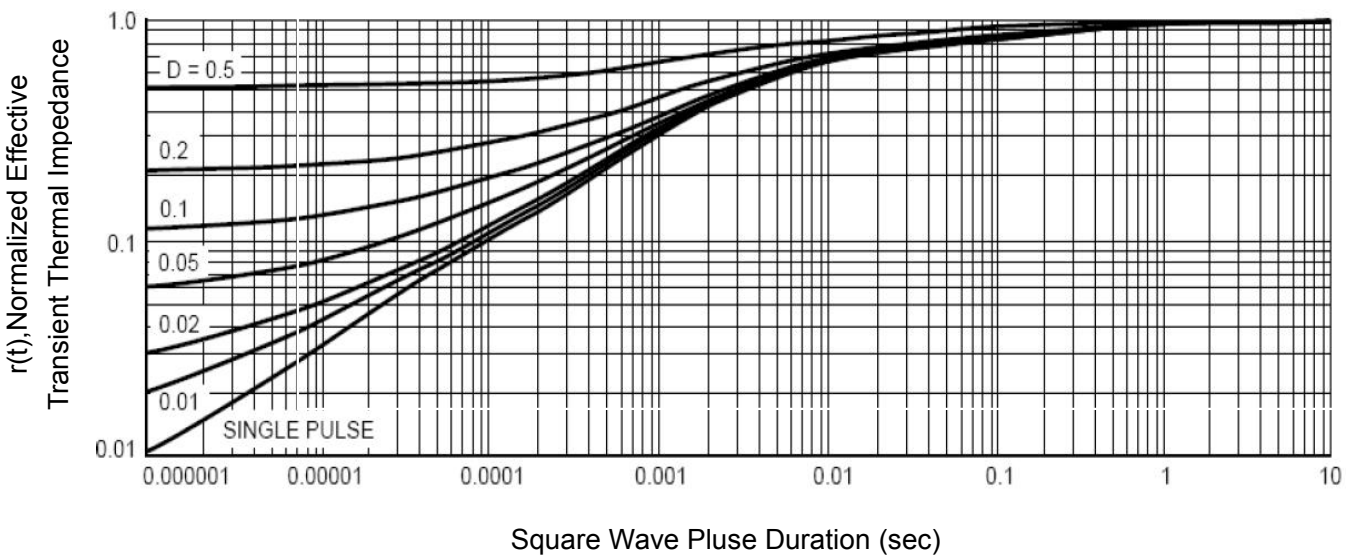


Figure 11 Normalized Maximum Transient Thermal Impedance